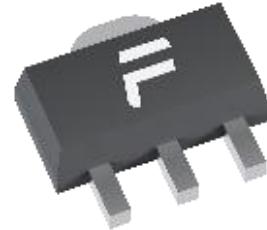
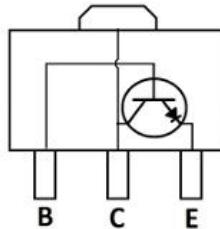


SOT-89-3L Bipolar Transistor 双极型三极管

■ Features 特点

NPN Low equivalent on-resistance 低等效电阻



■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V_{CBO}	170	V
Collector-Emitter Voltage 集电极发射极电压	V_{CEO}	150	V
Emitter-Base Voltage 发射极基极电压	V_{EBO}	7	V
Collector Current 集电极电流	I_C	1000	mA
Collector Pulse Current 集电极脉冲电流	I_{CM}	2000	mA
Power dissipation 耗散功率	$P_C(T_a=25^\circ\text{C})$	500	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	250	°C/W
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55 to +150 °C	

■ Device Marking 产品打标

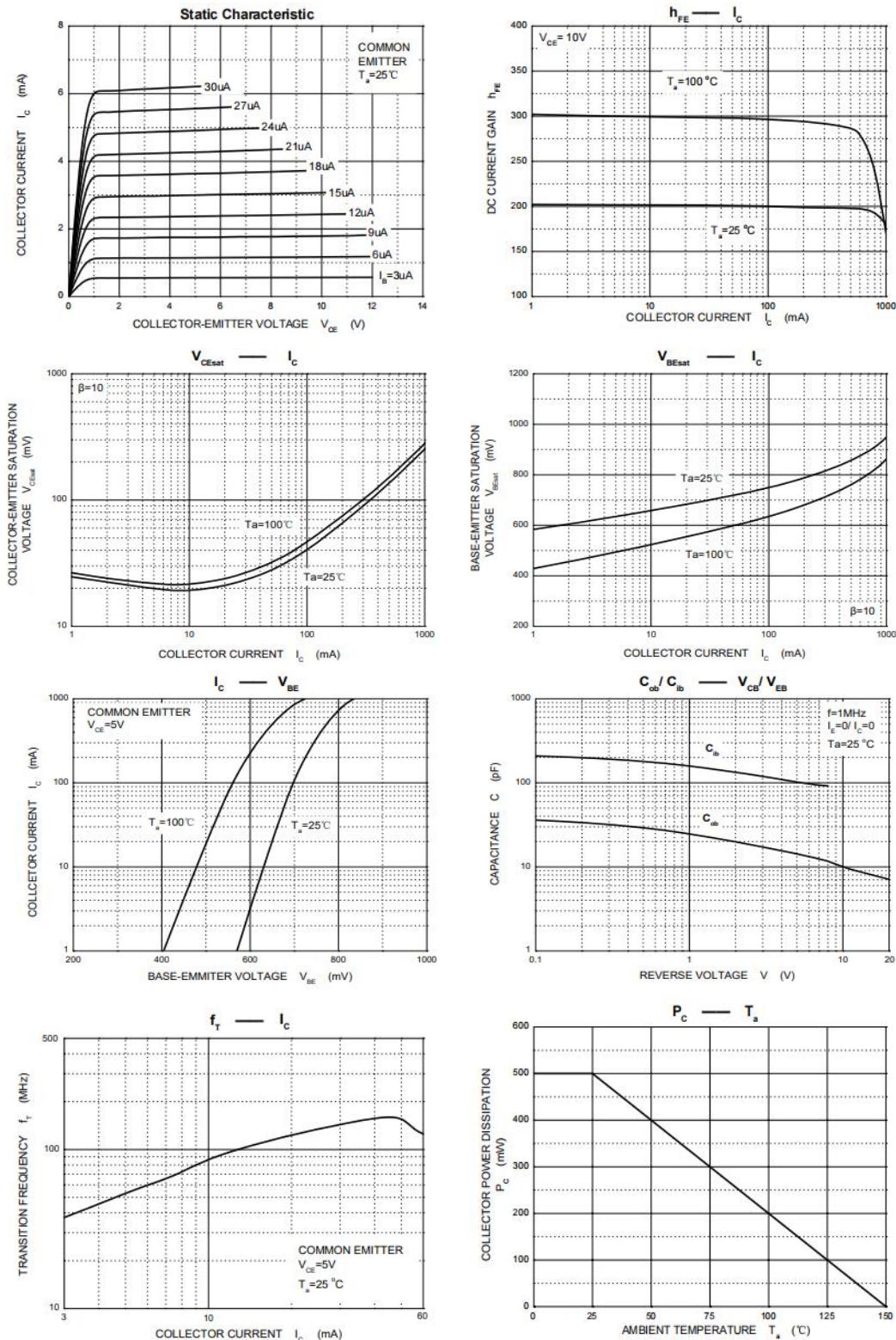
FCX495=495

■ Electrical Characteristics 电特性

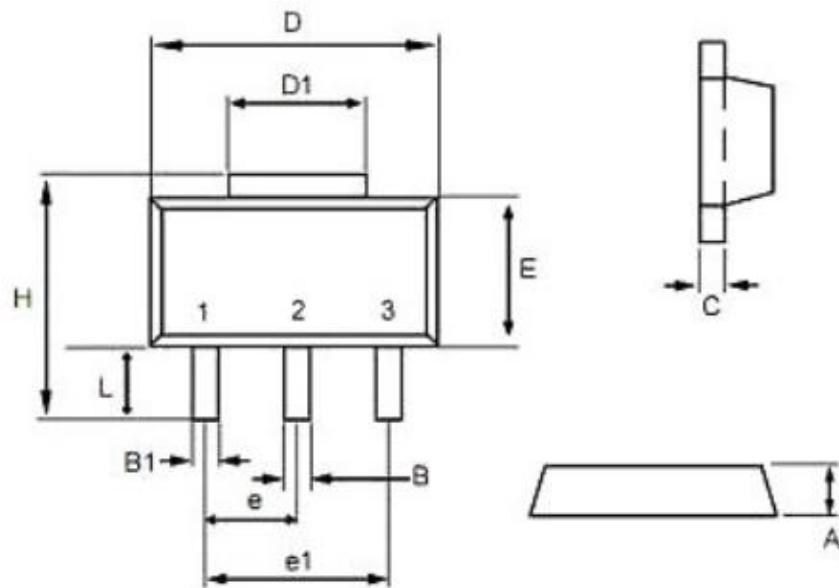
($T_A=25^\circ\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压($I_C= 100\mu\text{A}, I_E=0$)	BV_{CBO}	170	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压($I_C= 10\text{mA}, I_B=0$)	BV_{CEO}	150	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压($I_E= 100\mu\text{A}, I_C=0$)	BV_{EBO}	7	—	—	V
Collector-Base Leakage Current 集电极基极漏电流($V_{\text{CB}}= 150\text{V}, I_E=0$)	I_{CBO}	—	—	100	nA
Collector-Emitter Leakage Current 集电极发射极漏电流($V_{\text{CE}}= 150\text{V}, V_{\text{BE}}= 0\text{V}$)	I_{CES}	—	—	100	nA
Emitter-Base Leakage Current 发射极基极漏电流($V_{\text{EB}}= 5\text{V}, I_C=0$)	I_{EBO}	—	—	100	nA
DC Current Gain($V_{\text{CE}}= 10\text{V}, I_C= 1\text{mA}$) 直流电流增益($V_{\text{CE}}= 10\text{V}, I_C= 250\text{mA}$) ($V_{\text{CE}}= 10\text{V}, I_C= 500\text{mA}$) ($V_{\text{CE}}= 10\text{V}, I_C= 1000\text{mA}$)	H_{FE}	100 100 50 10	—	300	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降 ($I_C= 250\text{mA}, I_B= 25\text{mA}$) ($I_C= 500\text{mA}, I_B= 50\text{mA}$)	$V_{\text{CE}(\text{sat})}$	—	—	0.2 0.3	V
Base-Emitter Saturation Voltage 基极发射极饱和压降 ($I_C= 500\text{mA}, I_B= 50\text{mA}$)	$V_{\text{BE}(\text{sat})}$	—	—	1	V
Base-Emitter On Voltage 基极发射极导通电压 ($V_{\text{CE}}= 10\text{V}, I_C= 500\text{mA}$)	$V_{\text{BE}(\text{on})}$	—	—	1	V
Transition Frequency 特征频率($V_{\text{CE}}= 10\text{V}, I_C= 50\text{mA}$)	f_T	100	—	—	MHz
Output Capacitance 输出电容($V_{\text{CB}}= 10\text{V}, I_E=0, f=1\text{MHz}$)	C_{ob}	—	10	—	pF

■Typical Characteristic Curve 典型特性曲线



■ Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.40	1.60	0.055	0.063
B	0.40	0.56	0.016	0.022
B1	0.35	0.48	0.014	0.019
C	0.35	0.44	0.014	0.017
D	4.40	4.60	0.173	0.181
D1	1.35	1.83	0.053	0.072
e	1.45	1.55	0.057	0.061
e1	2.95	3.05	0.116	0.120
E	2.29	2.60	0.090	0.102
H	3.75	4.25	0.148	0.167
L	0.80	1.20	0.031	0.047